



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No. 740819-000442

Serial No.: 09/692,211

Page 1  
*#10 format b  
GSE  
Attn:  
6/14/02*

In re Patent Application of

)

Akihiko ISHIBASHI et al.

)

Art Unit: 2812

Serial No. 09/692,211

)

Filed: October 20, 2000

)

Examiner: S. MULPURI

For: METHOD OF FABRICATING

)

NITRIDE SEMICONDUCTOR DEVICE

)

*TS  
7-17*

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to Commissioner for Patents, Washington, DC 20231 on May 13, 2002.

*Deborah T. Tomme*

Deborah T. Tomme

RECEIVED  
U.S. PATENT AND  
TRADEMARK OFFICE  
MAY 13 2002

AMENDMENT UNDER 37 C.F.R. 1.116**BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

The following is presented in response to the Office Action mailed February 12, 2002, in connection with the above-captioned patent application.

**IN THE CLAIMS:**

Please cancel claims 1, 2, 3, 9 and 12.

Please amend claims 4-8 as follows.

4. (Amended) The method of fabricating a nitride semiconductor device of claim 13, wherein said second growth ambient pressure is a pressure higher than the atmospheric pressure.

*B1 cont*

5. (Amended) The method of fabricating a nitride semiconductor device of claim 4, wherein said second nitride semiconductor layer includes indium.